

1 48. (Amended) A semiconductor processing method of chemical  
2 vapor depositing SiO<sub>2</sub> on a substrate comprising:

3 placing a substrate within a hot wall low pressure chemical vapor  
4 deposition reactor;

5 feeding an organic silicon precursor into the hot wall chemical  
6 vapor deposition reactor having the substrate positioned therein [under  
7 conditions effective to decompose the precursor into SiO<sub>2</sub> which deposits  
8 on the substrate and into a gaseous oxide of hydrogen]; [and]

9 feeding an additional quantity of the gaseous oxide of hydrogen  
10 into the hot wall low pressure chemical vapor deposition reactor while  
11 feeding the organic silicon precursor into the reactor, wherein the  
12 organic silicon precursor and the additional quantity of the gaseous oxide  
13 of hydrogen are fed into the reactor from separate feed streams; and  
14 providing conditions effective to decompose the precursor into SiO<sub>2</sub>  
15 at a theoretical decomposition rate and effective to cause the additional  
16 quantity of gaseous oxide of hydrogen to reduce the theoretical  
17 decomposition rate to a lower actual decomposition rate.

18  
19 REMARKS

20 Claims 43, 44, 46 and 48 are amended. Claim 48 is amended to  
21 recite a "theoretical decomposition rate" and an "actual decomposition  
22 rate." Such amendments are supported in the specification at page 7,  
23 line 15 through page 10, line 2. A process providing for the